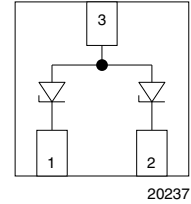
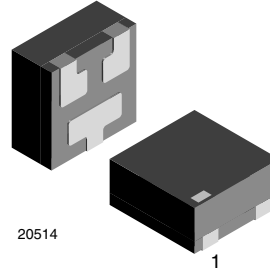




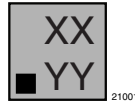
## Two-Line ESD-Protection in LLP75

### Features

- Two-line ESD-protection device
- ESD-immunity acc. IEC 61000-4-2
  - ± 30 kV contact discharge
  - ± 30 kV air discharge
- Space saving LLP package
- Lead (Pb)-free component
- Lead finish = "e3" = matte tin (Sn)
- Non-magnetic
- "Green" molding compound
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### Marking (example only)



Dot = Pin 1 marking  
 XX = Date code  
 YY = Type code (see table below)

### Ordering Information

Device name	Ordering code	Taped units per reel (8 mm tape on 7" reel)	Minimum order quantity
GSOT03C-HT3	GSOT03C-HT3-GS08	3000	15000
GSOT04C-HT3	GSOT04C-HT3-GS08	3000	15000
GSOT05C-HT3	GSOT05C-HT3-GS08	3000	15000
GSOT08C-HT3	GSOT08C-HT3-GS08	3000	15000
GSOT12C-HT3	GSOT12C-HT3-GS08	3000	15000
GSOT15C-HT3	GSOT15C-HT3-GS08	3000	15000
GSOT24C-HT3	GSOT24C-HT3-GS08	3000	15000
GSOT36C-HT3	GSOT36C-HT3-GS08	3000	15000

### Package Data

Device name	Package name	Marking code	Weight	Molding compound flammability rating	Moisture sensitivity level	Soldering conditions
GSOT03C-HT3	LLP75-3B	03	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT04C-HT3	LLP75-3B	04	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT05C-HT3	LLP75-3B	05	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT08C-HT3	LLP75-3B	08	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT12C-HT3	LLP75-3B	12	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT15C-HT3	LLP75-3B	15	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT24C-HT3	LLP75-3B	24	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT36C-HT3	LLP75-3B	36	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals

# GSOT03C-HT3 to GSOT36C-HT3



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## Absolute Maximum Ratings GSOT03C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	369	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	504	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$

## GSOT04C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	429	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	564	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$

## GSOT05C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	480	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	612	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$



# GSOT03C-HT3 to GSOT36C-HT3

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## GSOT08C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	18	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	18	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	345	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	400	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$

## GSOT12C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	12	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	12	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	312	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	337	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$

## GSOT15C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	8	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	8	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	230	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	245	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$

# GSOT03C-HT3 to GSOT36C-HT3



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## GSOT24C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	5	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	5	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	235	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	240	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$

## GSOT36C-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	3.5	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	3.5	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	248	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected Acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	252	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}C$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}C$

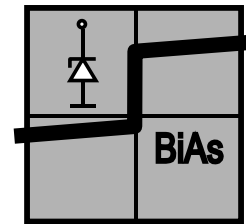
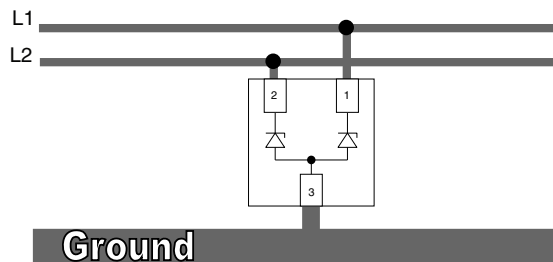
## **BiAs-Mode (2-line Bidirectional Asymmetrical protection mode)**

With the **GSOTxxC-HT3** two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified **Maximum Reverse Working Voltage** ( $V_{RWM}$ ) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offer a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The **Clamping Voltage** ( $V_C$ ) is defined by the **Breakthrough Voltage** ( $V_{BR}$ ) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low **Forward Voltage** ( $V_F$ ) clamps the negative transient close to the ground level.

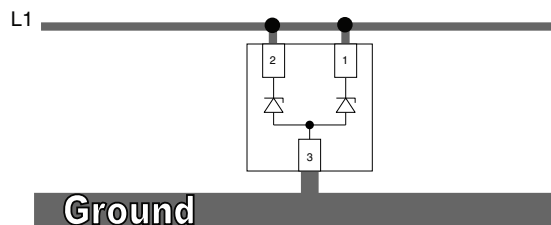
Due to the different clamping levels in forward and reverse direction the **GSOTxxC-HT3** clamping behaviour is **Bidirectional** and **Asymmetrical (BiAs)**.



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If a higher surge current or **Peak Pulse current** ( $I_{PP}$ ) is needed, both protection diodes in the **GSOTxxC-HT3** can also be used in parallel in order to "double" the performance.

- This offers:
- double surge power = double peak pulse current ( $2 \times I_{PPM}$ )
  - halve line inductance = reduced clamping voltage
  - halve line resistance = reduced clamping voltage
  - double **Diode Capacitance** ( $2 \times C_D$ )
  - double **Reverse leakage current** ( $2 \times I_R$ )



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# GSOT03C-HT3 to GSOT36C-HT3



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## Electrical Characteristics

Ratings at 25 °C, ambient temperature unless otherwise specified

### GSOT03C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 100 \mu A$	$V_{RWM}$	3.3			V
Reverse current	at $V_R = 3.3 V$	$I_R$			100	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	4	4.6		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		5.7	7.5	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		10	12.3	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_F$		4.5		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		420	600	pF
	at $V_R = 1.6 V$ ; $f = 1 MHz$	$C_D$		260		pF

### GSOT04C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 20 \mu A$	$V_{RWM}$	4			V
Reverse current	at $V_R = 4 V$	$I_R$			20	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	5	6.1		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		7.5	9	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		11.2	14.3	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_F$		4.5		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		310	450	pF
	at $V_R = 2 V$ ; $f = 1 MHz$	$C_D$		200		pF

### GSOT05C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 10 \mu A$	$V_{RWM}$	5			V
Reverse current	at $V_R = 5 V$	$I_R$			10	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	6	6.8		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		7	8.7	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		12	16	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_F$		4.5		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		260	350	pF
	at $V_R = 2.5 V$ ; $f = 1 MHz$	$C_D$		150		pF



# GSOT03C-HT3 to GSOT36C-HT3

Vishay Semiconductors

## GSOT08C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 5 \mu A$	$V_{RWM}$	8			V
Reverse current	at $V_R = 8 V$	$I_R$			5	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	9	10		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		10.7	13	V
	at $I_{PP} = I_{PPM} = 18 A$	$V_C$		15.2	19.2	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 18 A$	$V_F$		3		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		160	250	pF
	at $V_R = 4 V$ ; $f = 1 MHz$	$C_D$		80		pF

## GSOT12C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	12			V
Reverse current	at $V_R = 12 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	13.5	15		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		15.4	18.7	V
	at $I_{PP} = I_{PPM} = 12 A$	$V_C$		21.2	26	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 12 A$	$V_F$		2.2		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		115	150	pF
	at $V_R = 6 V$ ; $f = 1 MHz$	$C_D$		50		pF

## GSOT15C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	15			V
Reverse current	at $V_R = 15 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	16.5	18		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		19.4	23.5	V
	at $I_{PP} = I_{PPM} = 8 A$	$V_C$		24.8	28.8	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 8 A$	$V_F$		1.8		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		90	120	pF
	at $V_R = 7.5 V$ ; $f = 1 MHz$	$C_D$		35		pF

# GSOT03C-HT3 to GSOT36C-HT3



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## GSOT24C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	24			V
Reverse current	at $V_R = 24 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	27	30		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		34	41	V
	at $I_{PP} = I_{PPM} = 5 A$	$V_C$		41	47	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 5 A$	$V_F$		1.4		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		65	80	pF
	at $V_R = 12 V$ ; $f = 1 MHz$	$C_D$		20		pF

## GSOT36C-HT3

BiAs mode (between pin 1 to 3 or pin 2 to 3)

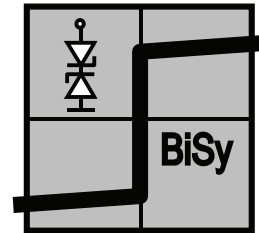
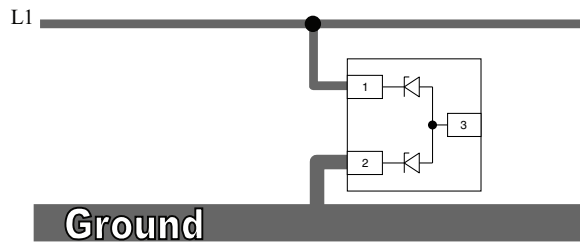
Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			2	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	36			V
Reverse current	at $V_R = 36 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	39	43		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		49	60	V
	at $I_{PP} = I_{PPM} = 3.5 A$	$V_C$		59	71	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 3.5 A$	$V_F$		1.3		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		52	65	pF
	at $V_R = 18 V$ ; $f = 1 MHz$	$C_D$		12		pF

## BiSy-mode (1-line Bidirectional Symmetrical protection mode)

If a bipolar symmetrical protection device is needed the **GSOTxxC-HT3** can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). pin 3 must not be connected.

Positive and negative voltage transients will be clamped in the same way. The clamping current through the **GSOTxxC-HT3** passes one diode in forward direction and the other one in reverse direction. The **Clamping Voltage ( $V_C$ )** is defined by the **Breakthrough Voltage ( $V_{BR}$ )** level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the **GSOTxxC-HT3** voltage clamping behaviour is **Bidirectional** and **Symmetrical (BiSy)**.



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## Electrical Characteristics

Ratings at 25 °C, ambient temperature unless otherwise specified

### GSOT03C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 100 \mu A$	$V_{RWM}$	3.8			V
Reverse current	at $V_R = 3.8 V$	$I_R$			100	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	4.5	5.3		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		7	8.4	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		14	16.8	V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		210	300	pF
	at $V_R = 1.6 V$ ; $f = 1 MHz$	$C_D$		190		pF

### GSOT04C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 20 \mu A$	$V_{RWM}$	4.5			V
Reverse current	at $V_R = 4.5 V$	$I_R$			20	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	5.5	6.8		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		7.5	9	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		15.7	18.8	V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		155	225	pF
	at $V_R = 2 V$ ; $f = 1 MHz$	$C_D$		135		pF

# GSOT03C-HT3 to GSOT36C-HT3



Vishay Semiconductors

## GSOT05C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 10 \mu A$	$V_{RWM}$	5.5			V
Reverse current	at $V_R = 5.5 V$	$I_R$			10	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	6.5	7.5		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		8.1	9.7	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		17	20.4	V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		130	175	pF
	at $V_R = 2.5 V$ ; $f = 1 MHz$	$C_D$		100		pF

## GSOT08C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 5 \mu A$	$V_{RWM}$	8.5			V
Reverse current	at $V_R = 8.5 V$	$I_R$			5	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	9.5	10.7		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		11.7	14	V
	at $I_{PP} = I_{PPM} = 18 A$	$V_C$		18.5	22.2	V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		80	125	pF
	at $V_R = 4 V$ ; $f = 1 MHz$	$C_D$		60		pF

## GSOT12C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	12.5			V
Reverse current	at $V_R = 12.5 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	13.5	15.7		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		16.4	19.7	V
	at $I_{PP} = I_{PPM} = 12 A$	$V_C$		23.4	28.1	V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		58	75	pF
	at $V_R = 6 V$ ; $f = 1 MHz$	$C_D$		36		pF

## GSOT15C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	15.5			V
Reverse current	at $V_R = 15.5 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	17	18.7		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		20.4	24.5	V
	at $I_{PP} = I_{PPM} = 8 A$	$V_C$		26.6	30.6	V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		45	60	pF
	at $V_R = 7.5 V$ ; $f = 1 MHz$	$C_D$		25		pF

## GSOT24C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

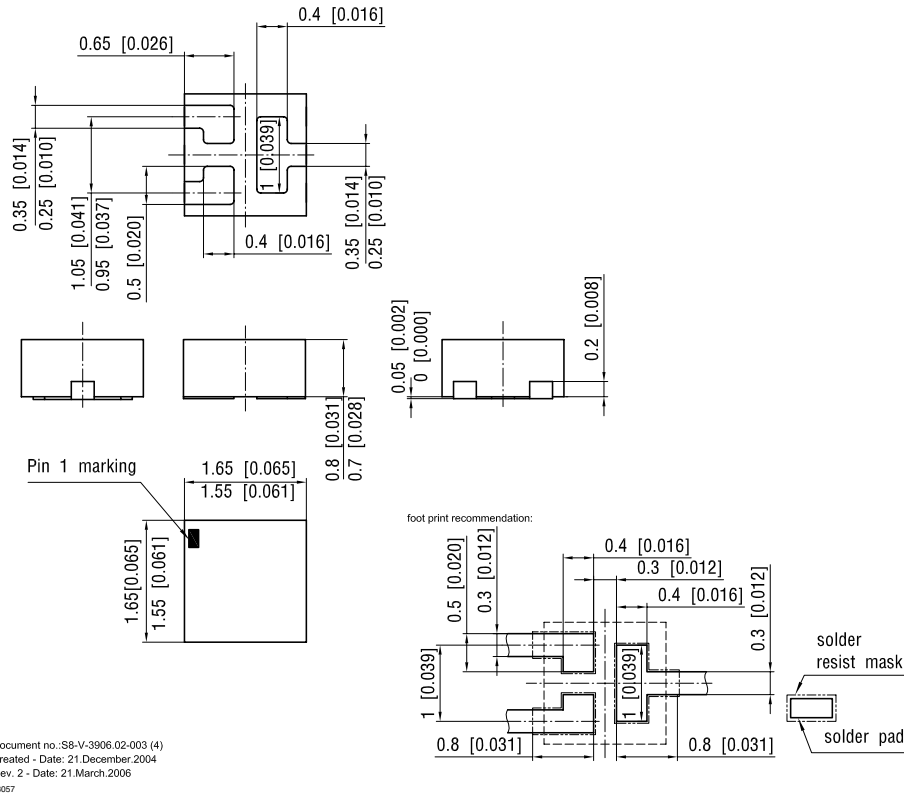
Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	24.5			V
Reverse current	at $V_R = 24.5 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	27.5	30.7		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		34	41	V
	at $I_{PP} = I_{PPM} = 5 A$	$V_C$		40	48	V
Capacitance	at $V_R = 0 V; f = 1 MHz$	$C_D$		33	40	pF
	at $V_R = 12 V; f = 1 MHz$	$C_D$		18		pF

## GSOT36C-HT3

BiSy mode (between pin 1 to 2 or pin 2 to 1; pin 3 not connected)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	36.5			V
Reverse current	at $V_R = 36.5 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	39.5	43.7		V
Clamping voltage	at $I_{PP} = 1 A$	$V_C$		50	60	V
	at $I_{PP} = I_{PPM} = 3.5 A$	$V_C$		60	72	V
Capacitance	at $V_R = 0 V; f = 1 MHz$	$C_D$		26	33	pF
	at $V_R = 18 V; f = 1 MHz$	$C_D$		10		pF

## Package Dimensions in millimeters (inches): LLP75-3B



Document no.: 58-V-3996-02-003 (4)  
 Created - Date: 21 December 2004  
 Rev. 2 - Date: 21 March 2006  
 18057

### Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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